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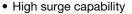
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# Thyristor High Voltage, Phase Control SCR, 70 A

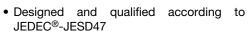


PRODUCT SUMMARY					
Package	Super TO-247				
Diode variation	Single SCR				
I <sub>T(AV)</sub>	70 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V, 1600 V				
$V_{TM}$	1.25 V				
I <sub>GT</sub>	100 mA				
$T_J$	-40 °C to 125 °C				

#### **FEATURES**







 Material categorization: For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



(e3)

#### RoHS COMPLIANT

#### **APPLICATIONS**

- · AC switches
- High voltage input rectification (soft start)
- · High current crow-bar
- · Other phase-control circuits
- Designed to be used with Vishay input diodes, switches, and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-70TPS..PbF high voltage series of silicon controlled rectifiers are specifically designed for high and medium power switching, and phase control applications.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I <sub>T(AV)</sub>	Sinusoidal waveform	70	A			
I <sub>RMS</sub>	Lead current limitation	75	A			
V <sub>RRM</sub> /V <sub>DRM</sub>	Range	1200/1600	V			
I <sub>TSM</sub>		1100	А			
V <sub>T</sub>	100 A, T <sub>J</sub> = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
TJ		-40 to 125	°C			

VOLTAGE RATINGS							
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA				
VS-70TPS12PbF	1200	1300	15				
VS-70TPS16PbF	1600	1700	15				



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PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 82 °C, 180° cor	nduction half sine wave		70	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>	Lead current limitation	Lead current limitation		75	Α
Maximum peak, one-cycle	<b></b>	10 ms sine pulse, rat	ted V <sub>RRM</sub> applied		930	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no	voltage reapplied		1100	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rat	ted V <sub>RRM</sub> applied	Initial $T_J = T_J$ maximum	4325	A <sup>2</sup> s
Maximum i-t for fusing	I-ί	10 ms sine pulse, no	voltage reapplied	maximam	6115	
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied		61 150	A²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>			0.916	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	T 105 °C	T <sub>J</sub> = 125 °C		1.21	v
Low level value of on-state slope resistance	r <sub>t1</sub>	1J= 125 G		4.138	<b></b> 0	
High level value of on-state slope resistance	r <sub>t2</sub>			3.43	mΩ	
Maximum peak on-state voltage	$V_{TM}$	100 A, T <sub>J</sub> = 25 °C		1.4	V	
Maximum rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C		150	A/μs	
Maximum holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		200		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		400		
Maritim and all all all all all all all all all al	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 25 °C	$V_R = Rated V_{RRM}/V_{DRM}$		1.0	mA
Maximum reverse and direct leakage current		$T_J = 125 ^{\circ}\text{C}$ ( $T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{M}$			15	
Maximum rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = 125 °C	V <sub>DRM</sub> = R <sub>g</sub> -k = Open)		500	V/µs

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>	T = 30 µs		10	w	
Maximum average gate power	P <sub>G(AV)</sub>	1 = 30 μs		2.5	vv	
Maximum peak gate current	I <sub>GM</sub>			2.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>			10		
	V <sub>GT</sub>	T <sub>J</sub> = - 40 °C		1.8	V	
Maximum required DC gate voltage to trigger		T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	1.5	V	
		T <sub>J</sub> = 125 °C		1.1		
		T <sub>J</sub> = - 40 °C		150		
Maximum required DC gate current to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	100	mA	
		T <sub>J</sub> = 125 °C		80		
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Poted volve		0.25	V	
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value		6	mA	

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction temperature range		TJ		-40 to 125	°C	
Maximum storage temperature	range	T <sub>Stg</sub>		-40 to 150		
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	0.27		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		40	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.2		
Approximate weight				6	g	
				0.21	oz.	
Marinting torque	minimum			6 (5)	kgf · cm	
Mounting torque -	maximum			12 (10)	(lbf · in)	
Marking device			Consist de Super TO 247	70TPS	512	
			Case style Super TO-247	70TPS	70TPS16	

$\Delta R_{thJ-hs}$ Conduction per junction											
DEVICE	s	SINE HALF WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION				LIMITO
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-70TPSPbF	0.078	0.092	0.117	0.172	0.302	0.053	0.092	0.125	0.180	0.306	°C/W

#### Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC

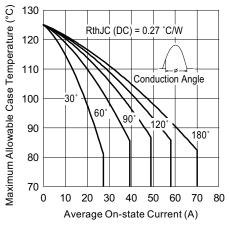


Fig. 1 - Current Rating Characteristics

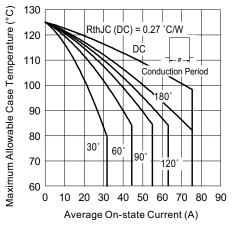


Fig. 2 - Current Rating Characteristics

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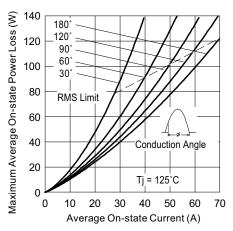


Fig. 3 - On-State Power Loss Characteristics

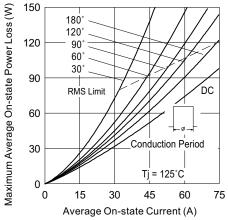


Fig. 4 - On-State Power Loss Characteristics

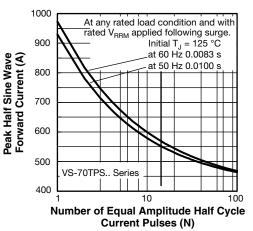


Fig. 5 - Maximum Non-Repetitive Surge Current

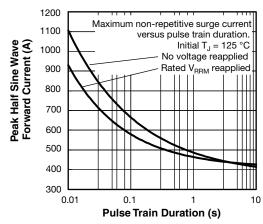


Fig. 6 - Maximum Non-Repetitive Surge Current

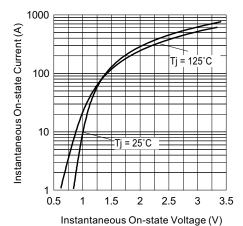
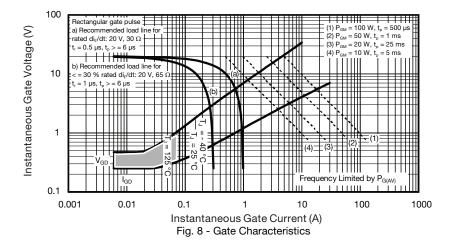


Fig. 7 - On-State Voltage Drop Characteristics

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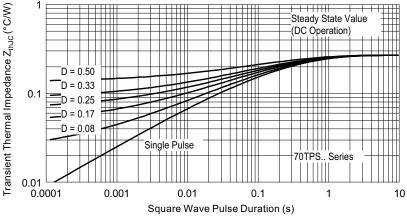


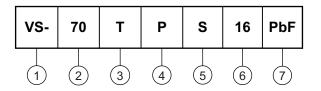
Fig. 9 - Thermal Impedance  $Z_{thJC}$  Characteristics

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#### **ORDERING INFORMATION TABLE**





1 - Vishay Semiconductors product

2 - Current rating (70 = 70 A)

3 - Circuit configuration:

T = Thyristor

4 - Package:

6

P = Super TO-247

5 - Type of silicon:

S = Standard recovery rectifier

- Voltage code x 100 = V<sub>RRM</sub> 12 = 1200 V 16 = 1600 V

7 - PbF = Lead (Pb)-free

 ORDERING INFORMATION (example)

 PREFERED P/N
 QUANTITY PER T/R
 MINIMUM ORDER QUANTITY
 PACKAGING DESCRIPTION

 VS-70TPS12PbF
 25
 500
 Antistatic plastic tube

 VS-70TPS16PbF
 25
 500
 Antistatic plastic tube

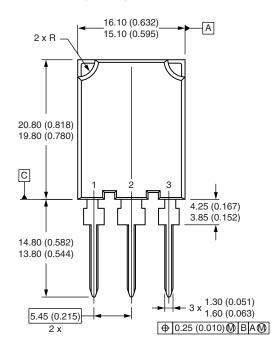
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95073</u>					
Part marking information	www.vishay.com/doc?95070				

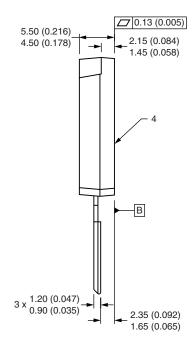


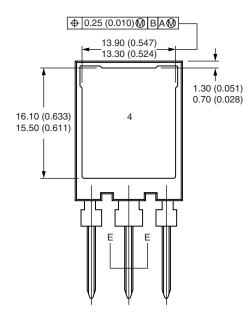
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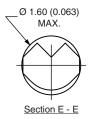
# Super TO-247

#### **DIMENSIONS** in millimeters (inches)









#### Lead assignments

MOSFET	<u>IGBT</u>
1 - Gate	1 - Gate
2 - Drain	2 - Collector
3 - Source	3 - Emitter
4 - Drain	4 - Collector

#### Notes

- (1) Dimension and tolerancing per ASME Y14.5M-1994
- (2) Controlling dimension: millimeter
- (3) Outline conforms to JEDEC® outline TO-274AA



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Revision: 02-Oct-12 Document Number: 91000

# AMEYA360 Components Supply Platform

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